

MA4X862

Silicon epitaxial planar type

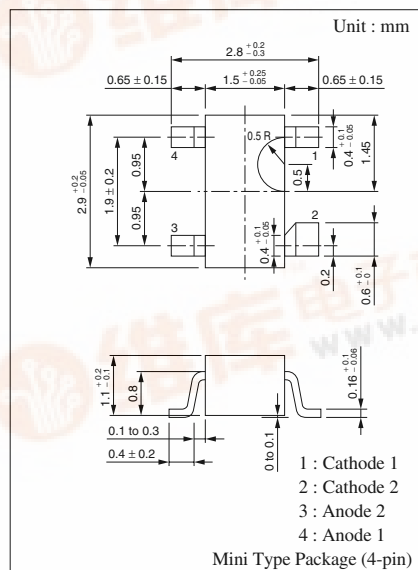
For band switching

■ Features

- Two electrically isolated elements incorporated
- Small diode capacitance C_D
- Low forward dynamic resistance r_f
- Optimum for a band switching of a tuner

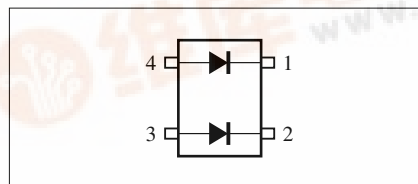
■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	35	V
Forward current (DC)	Single	100	mA
	Double	75	mA/Unit
Operating ambient temperature	T_{opr}	-25 to +85	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +100	$^\circ\text{C}$



Marking Symbol: M11

Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 33\text{ V}$			100	nA
Forward voltage (DC)	V_F	$I_F = 100\text{ mA}$			1.0	V
Diode capacitance	C_D	$V_R = 6\text{ V}$, $f = 1\text{ MHz}$			1.2	pF
Forward dynamic resistance	r_{f1}^{*1}	$I_F = 2\text{ mA}$, $f = 100\text{ MHz}$			0.65	Ω
	r_{f2}^{*2}				0.98	Ω

Note) 1. Rated input/output frequency: 100 MHz

2. *1 : r_f measuring instrument: Nihon Koshuha Model TDC-121A

*2 : r_f measuring instrument: YHP 4191A RF IMPEDANCE ANALYZER

